



T-39-05



2062

N-Channel MOS Silicon FET

Very High-Speed Switching Applications

©2842

Features

- Low ON resistance, very high-speed switching

Absolute Maximum Ratings at Ta = 25°C

		unit
Drain to Source Voltage	V _{DS}	250 V
Gate to Source Voltage	V _{GS}	±20 V
Drain Current (DC)	I _D	500 mA
Drain Current (Pulse)	I _{D peak}	1 A
Maximum Power Dissipation	P _D Mounted on ceramic PCB (250mm ² × 0.8mm)	1.5 W
	P _D Tc = 25°C	3.5 W
Junction Temperature	T _J	150 °C
Storage Temperature	T _{stg}	-55 to +150 °C

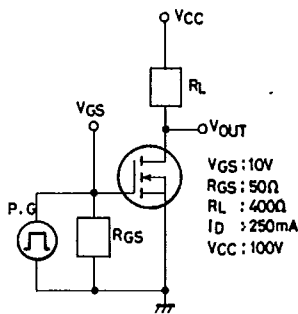
Electrical Characteristics at Ta = 25°C

		min	typ	max	unit
Drain to Source Breakdown Voltage	V _{DSS} I _D = 1mA, V _{GS} = 0	250			V
Drain to Source Cutoff Current	I _{DSS} V _{DS} = 250V, V _{GS} = 0			100	μA
Gate to Source Leakage Current	I _{GSS} V _{GS} = ±20V, V _{DS} = 0			±100	nA
Gate to Source Cutoff Voltage	V _{GS(off)} V _{DS} = 10V, I _D = 1mA	0.8		2.5	V
Forward Transfer Admittance	y _{fs} V _{DS} = 10V, I _D = 250mA	100	250		mS
Saturation Resistance	R _{DS(on)} I _D = 250mA, V _{GS} = 10V		6	9	Ω
Input Capacitance	C _{iss} V _{DS} = 20V, f = 1MHz		60		pF
Output Capacitance	C _{oss} V _{DS} = 20V, f = 1MHz		20		pF
Reverse Transfer Capacitance	C _{rss} V _{DS} = 20V, f = 1MHz		4		pF
Turn-ON Time	t _{on} I _D = 250mA, V _{GS} = 10V		25		ns
Turn-OFF Time	t _{off} I _D = 250mA, V _{GS} = 10V		60		ns

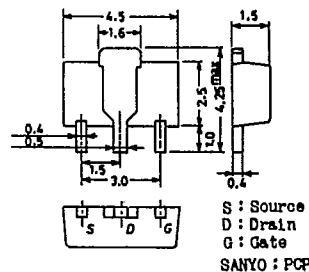


(Note) Be careful in handling the 2SK848 because it has no protection diode between gate and source.

Switching Time Test Circuit



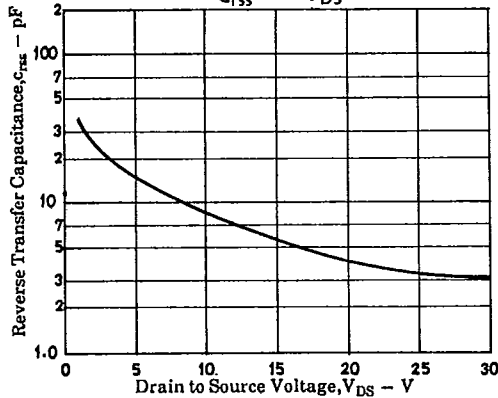
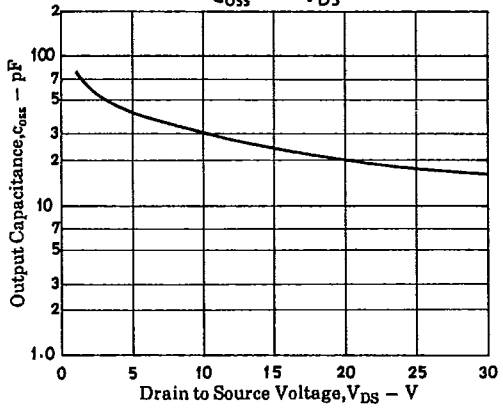
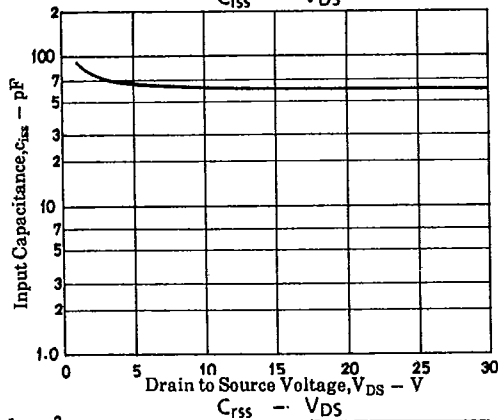
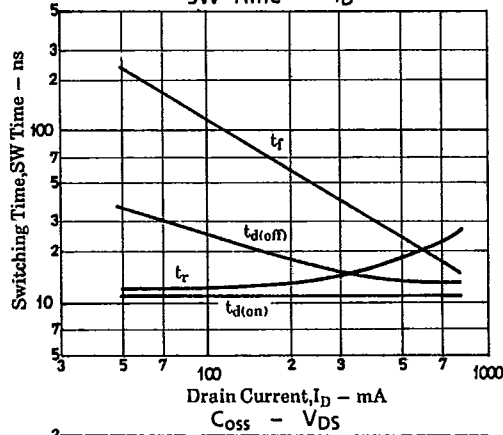
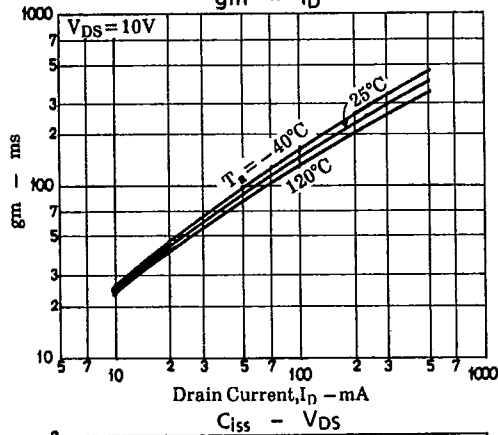
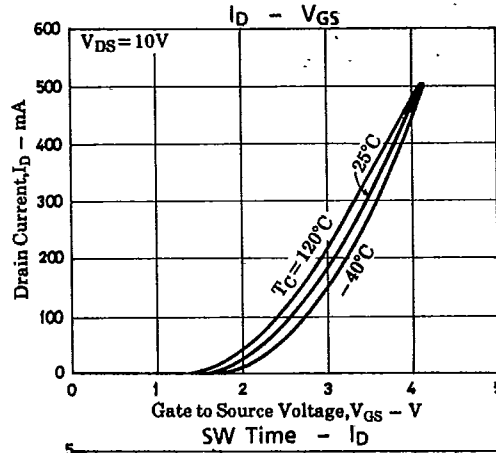
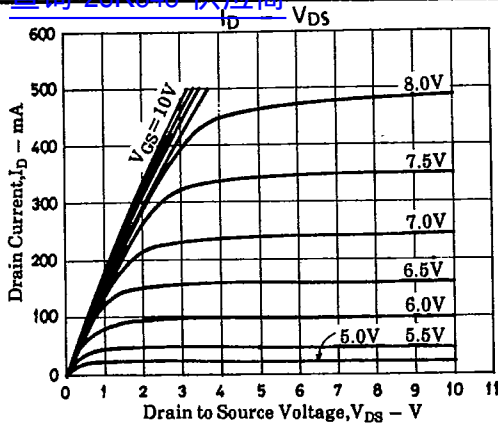
Case Outline 2062 (unit: mm)



2SK848

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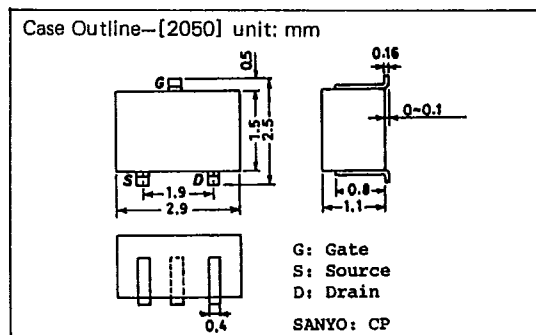
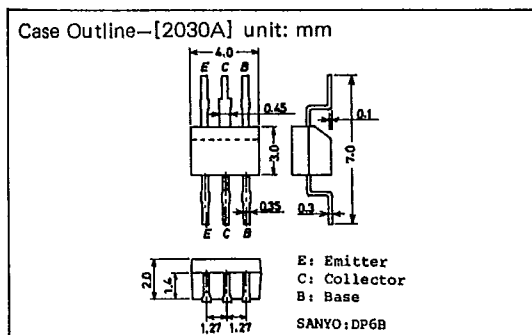
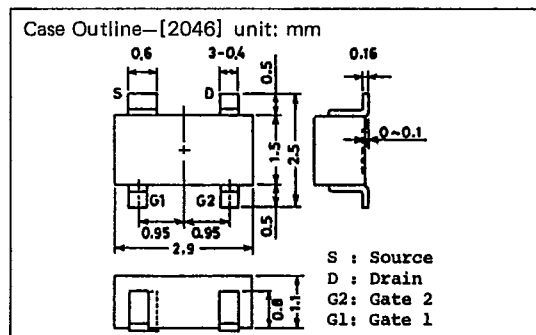
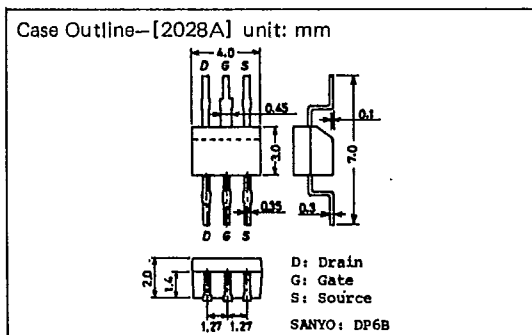
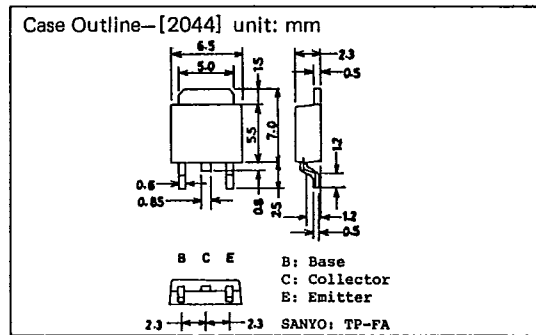
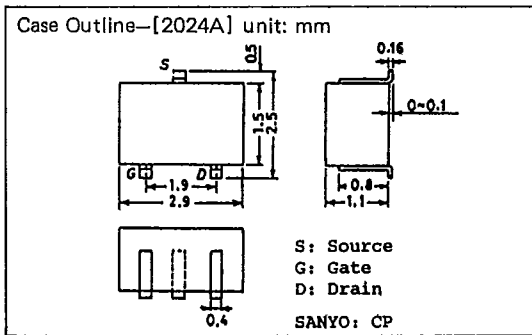
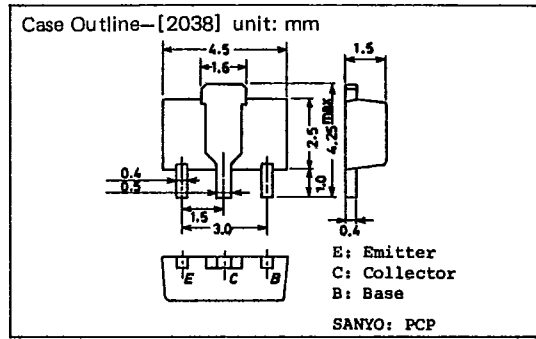
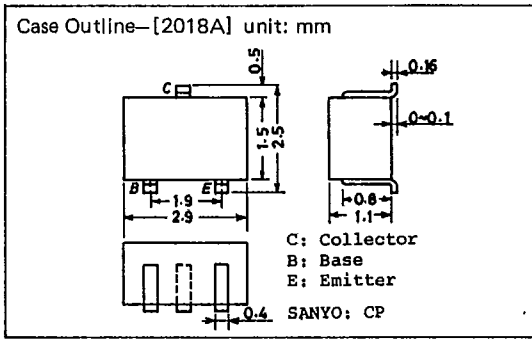


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CASE OUTLINES OF SURFACE MOUNT TRANSISTORS

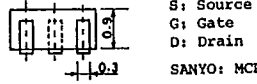
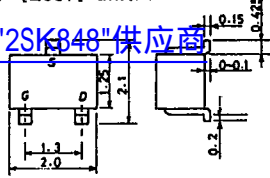
- All of Sanyo surface mount transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.



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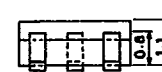
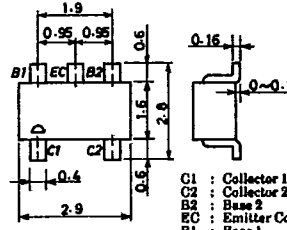
Case Outline—[2057] unit: mm

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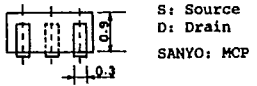
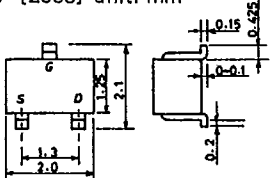
S: Source
G: Gate
D: Drain
SANYO: MCP

Case Outline—[2066] unit: mm



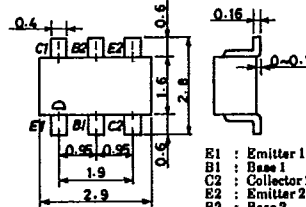
C1: Collector 1
C2: Collector 2
B2: Base 2
EC: Emitter Common
B1: Base 1
SANYO: CP6

Case Outline—[2058] unit: mm



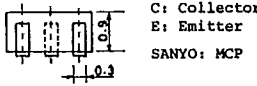
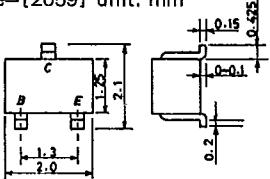
G: Gate
S: Source
D: Drain
SANYO: MCP

Case Outline—[2067] unit: mm



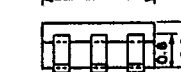
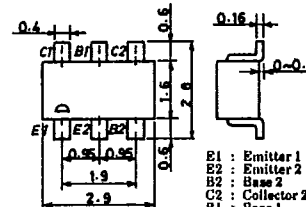
E1: Emitter 1
B1: Base 1
C2: Collector 2
E2: Emitter 2
B2: Base 2
C1: Collector 1
SANYO: CP6

Case Outline—[2059] unit: mm



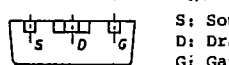
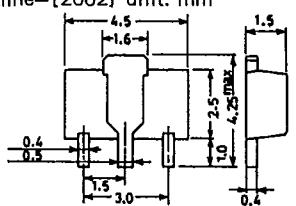
B: Base
C: Collector
E: Emitter
SANYO: MCP

Case Outline—[2068] unit: mm



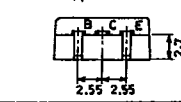
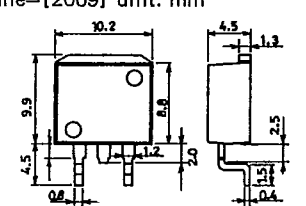
E1: Emitter 1
E2: Emitter 2
B2: Base 2
C2: Collector 2
B1: Base 1
C1: Collector 1
SANYO: CP6

Case Outline—[2062] unit: mm



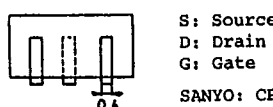
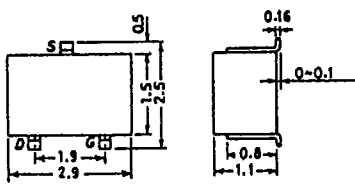
S: Source
D: Drain
G: Gate
SANYO: PCP

Case Outline—[2069] unit: mm



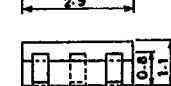
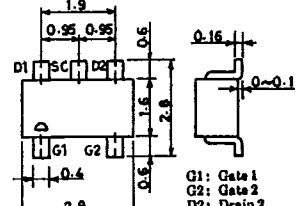
B: Base
C: Collector
E: Emitter
SANYO: SMP

Case Outline—[2065] unit: mm



S: Source
D: Drain
G: Gate
SANYO: CP

Case Outline—[2070] unit: mm



G1: Gate 1
G2: Gate 2
D2: Drain 2
SC: Source Common
D1: Drain 1
SANYO: CP6

